

## Package Top Phototransistor EAPST17086A0

### Features

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Package in 8mm tape on 7" diameter reels.
- Pb free
- The product itself will remain within RoHS compliant version.
- Compliance with EU REACH.
- Compliance Halogen Free .(Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm).

### Description

- EAPST17086A0 is a phototransistor in miniature SMD package which is molded in a water clear with flat top view lens. The device is Spectrally matched to visible and infrared emitting

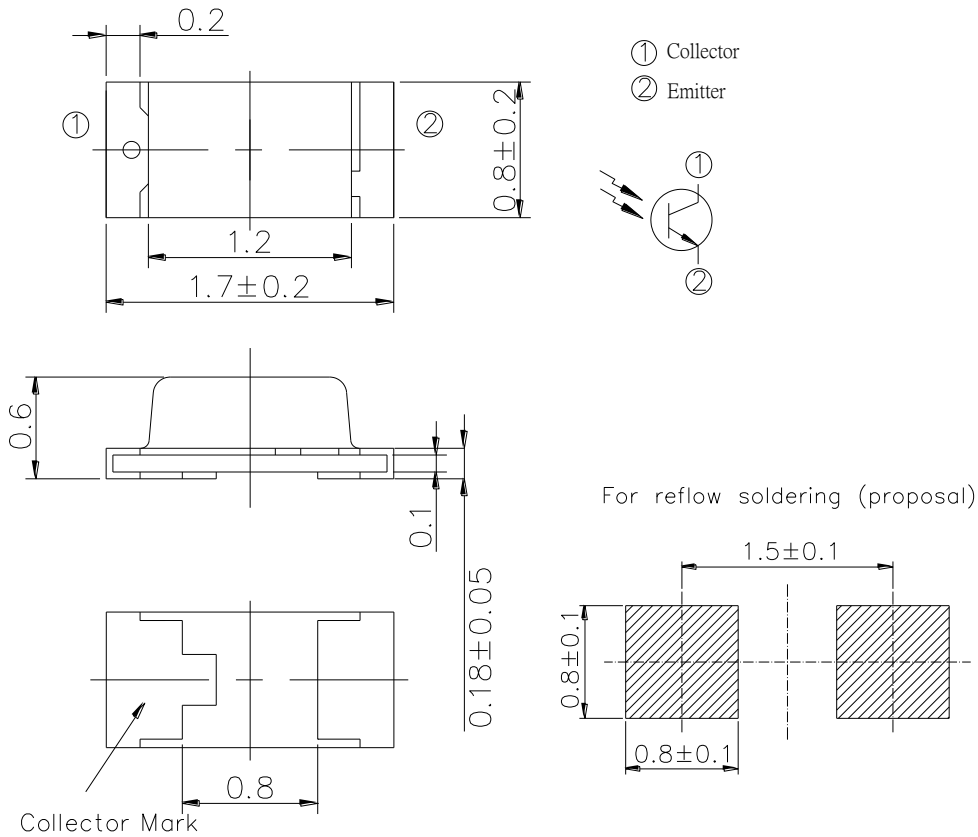
### Applications

- Miniature switch
- Counters and sorter
- Position sensor
- Infrared applied system

### Device Selection Guide

Device No.	Chip Material	Lens Color
EAPST17086A0	Silicon	Water clear

**Package Dimensions**



- Notes:** 1.All dimensions are in millimeters  
2.Tolerances unless dimensions  $\pm 0.1$ mm

**Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )**

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector-Voltage	$V_{ECO}$	5.5	V
Collector Current	$I_C$	20	mA
Operating Temperature	$T_{opr}$	-25 ~ +85	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 ~ +100	$^\circ\text{C}$
Soldering Temperature	$T_{sol}$	260	$^\circ\text{C}$
Power Dissipation at(or below) 25 $^\circ\text{C}$ Free Air Temperature	$P_c$	75	mW

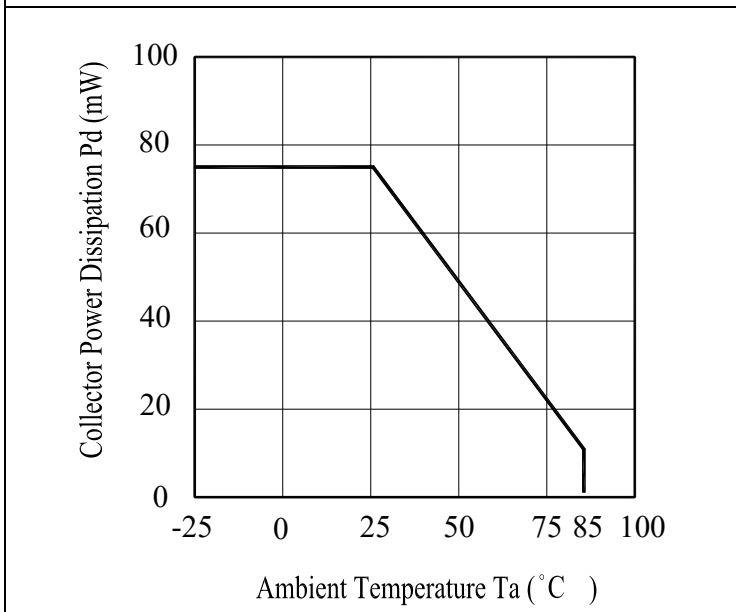
**Notes:** \*1:Soldering time  $\leq 5$  seconds.

**Electro-Optical Characteristics (Ta=25°C)**

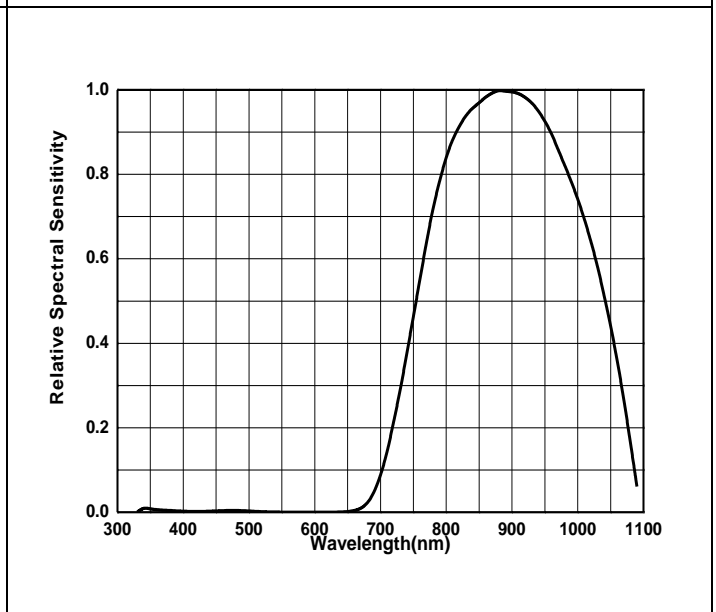
Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Rang Of Spectral Bandwidth	$\lambda_{0.5}$	760	---	1100	nm	---
Wavelength Of Peak Sensitivity	$\lambda_p$	---	940	---	nm	---
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	30	---	---	V	$I_C=100\mu A$ $E_e=0mW/cm^2$
Emitter-Collector Breakdown Voltage	$BV_{ECO}$	5	---	---	V	$I_E=100\mu A$ $E_e=0mW/cm^2$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	---	---	0.4	V	$I_C=2mA$ $E_e=1mW/cm^2$
Collector Dark Current	$I_{CEO}$	---	---	100	nA	$V_{CE}=20V$ $E_e=0mW/cm^2$
On State Collector Current	$I_{C(ON)}$	0.1	0.6	---	mA	$V_{CE}=5V$ $E_e=1mW/cm^2$ $\lambda_p=940nm$
Rise Time	$t_r$	---	15	---	$\mu S$	$V_{CE}=5V$ $I_C=1mA$ $R_L=1000\Omega$
Fall Time	$t_f$	---	15	---		

**Typical Electrical/Optical/Characteristics Curves**

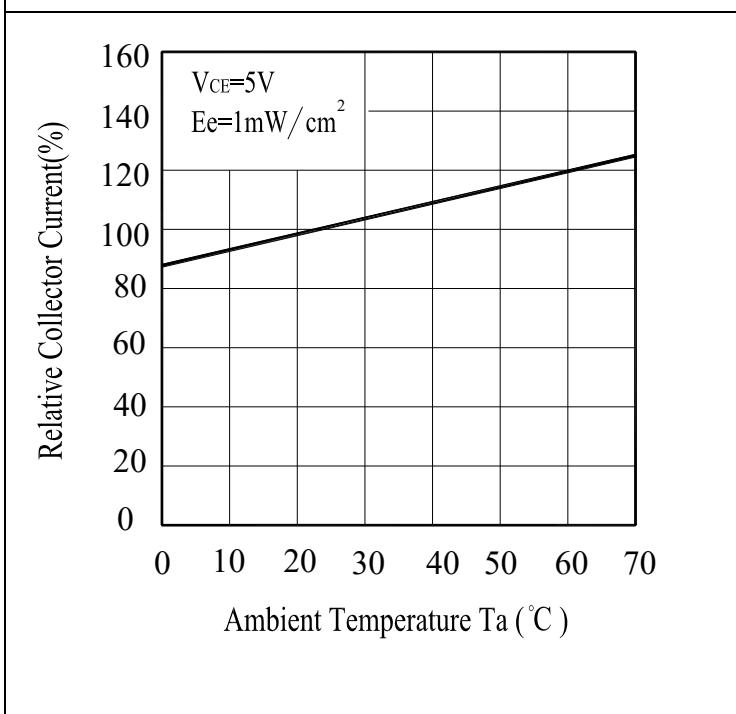
Collector Power Dissipation vs. Ambient Temperature



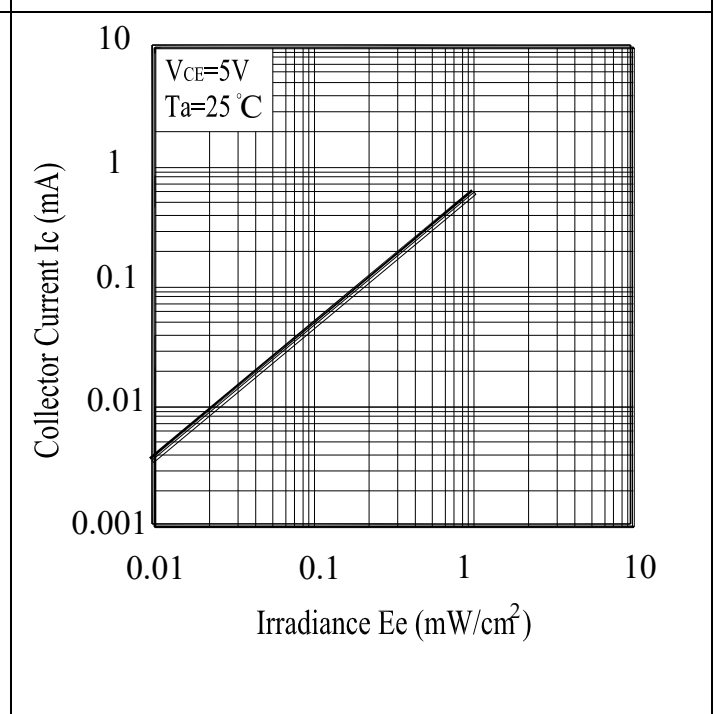
Spectral Sensitivity

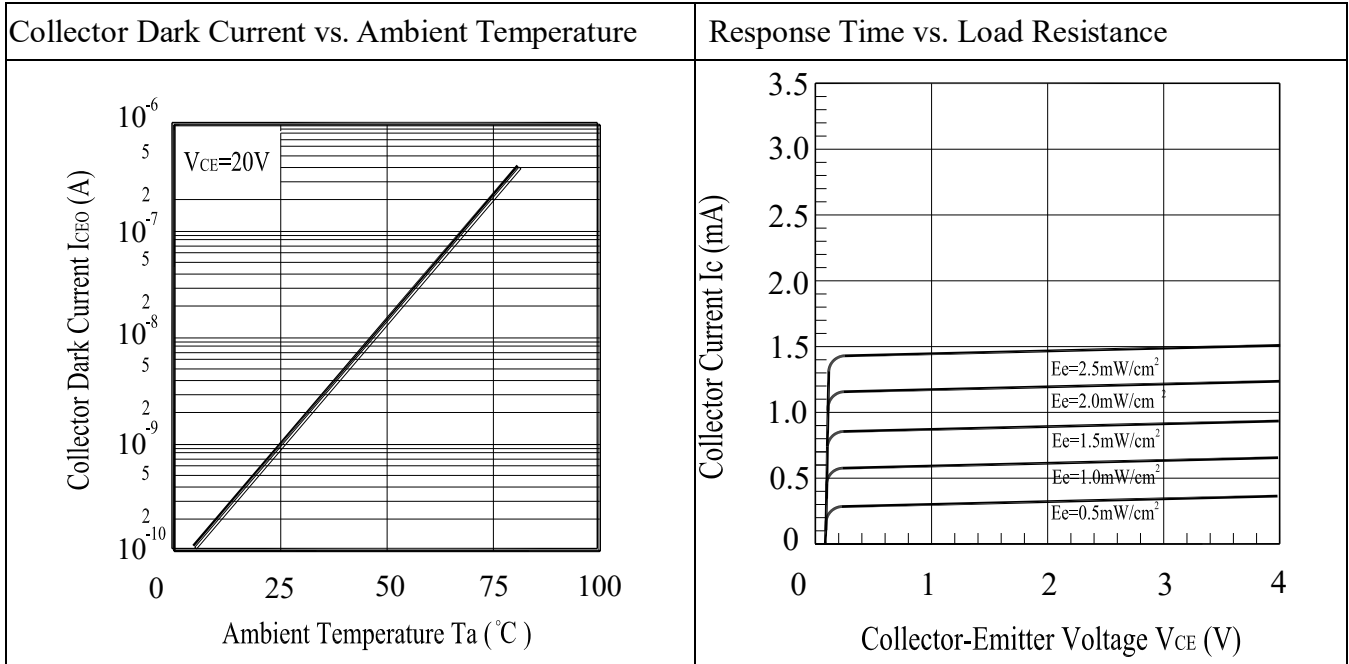


Relative Collector Current vs. Ambient Temperature



Collector Current vs. Irradiance





● **Precautions For Use**

1. Over-current-proof

Customer must apply resistors for protection , otherwise slight voltage shift will cause big current change ( Burn out will happen ).

2. Storage

2.1 Do not open moisture proof bag before the products are ready to use.

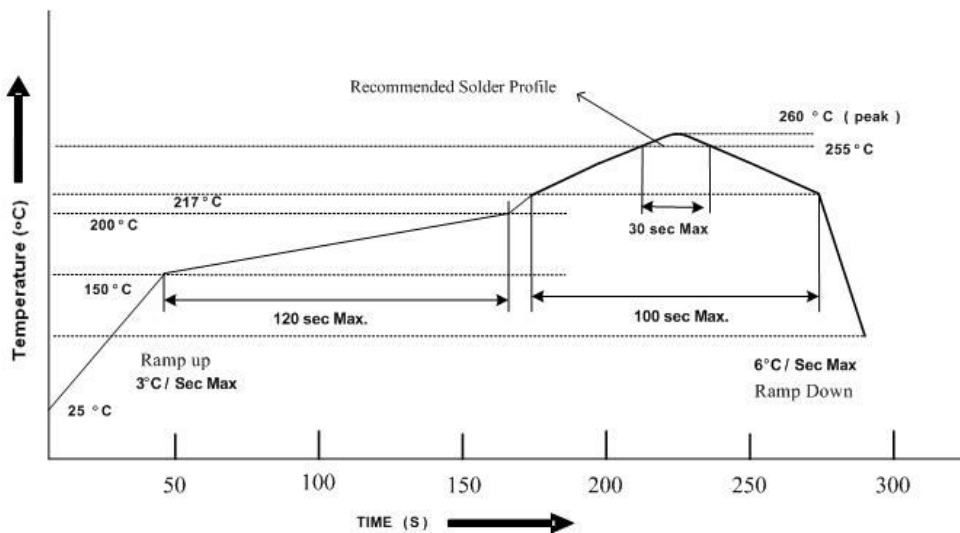
2.2 Shelf life in sealed bag from the bag seal date: 12 months at < 40°C and < 90% RH.

2.3 After opening the package, the Phototransiator must be kept at ≤ 30°C and ≤ 60%RH, and used within a year.

2.4 If the moisture absorbent material (silica gel) has faded away or the Phototransiator have exceeded the storage time. Baking treatment is required, refer to IPC/JEDEC J-STD-033 for bake procedure or recommend the conditions : 60±5°C for Min.24hrs.

3. Soldering Condition

3.1 Pb-free solder temperature profile



3.2 Reflow soldering should not be done more than two times.

3.3 When soldering, do not put stress on the Phototransiator during heating.

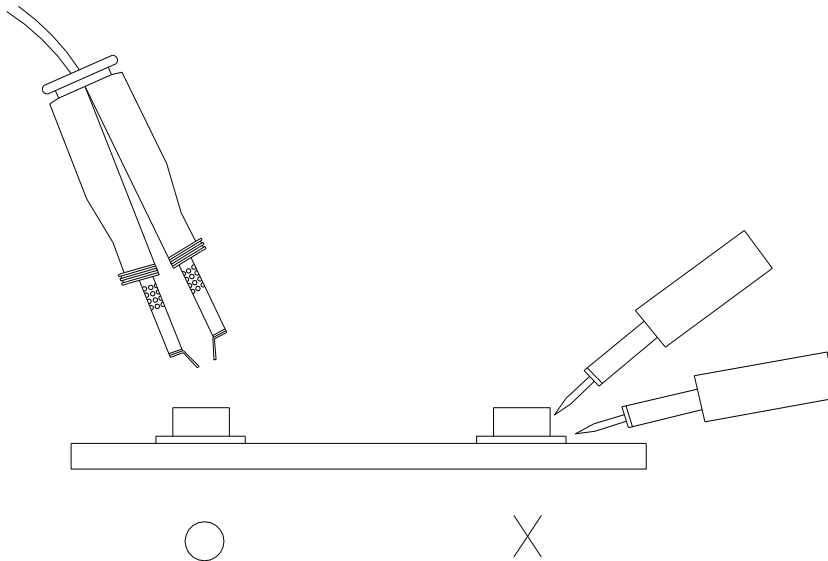
3.4 After soldering, do not warp the circuit board.

#### 4. Soldering Iron

Each terminal is to go to the tip of soldering iron temperature less than 350°C for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

#### 5. Repairing

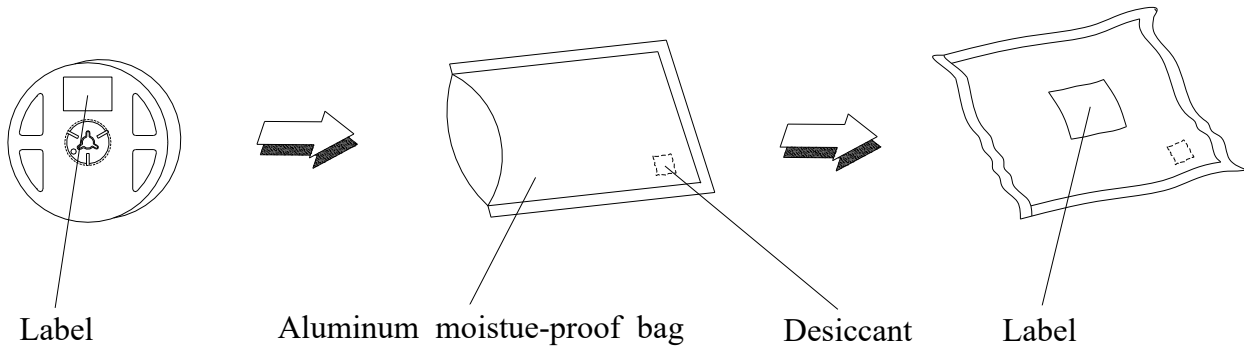
Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.



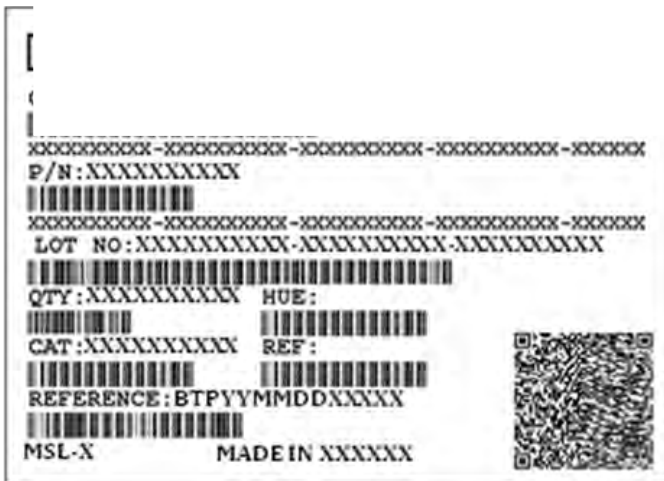




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**Label Form Specification**



CPN: Customer's Production Number  
 P/N : Production Number  
 QTY: Packing Quantity  
 CAT: Ranks  
 HUE: Peak Wavelength  
 REF: Reference  
 LOT No: Lot Number  
 MADE IN TAIWAN: Production Place

**DISCLAIMER**

1. EVERLIGHT reserves the right(s) on the adjustment of product material mix for the specification.
2. The product meets EVERLIGHT published specification for a period of twelve (12) months from date of shipment.
3. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
4. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from the use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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